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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Tsukasa Yajima

Group Art Unit: 2814

Serial No.: 09/768,271

Examiner: A. Mai

Filed: January 25, 2001

For: SEMICONDUCTOR DEVICE HAVING PROTECTIVE LAYER ON FIELD OXIDE

AMENDMENT UNDER 37 C.F.R. §1.116

Honorable Assistant Commissioner for Patents
Washington, D.C. 20231

Date: May 22, 2002

Sir:

In response to the Final Office Action dated February 22, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Claims:

The following replacement claims are respectfully submitted:

6. (Twice Amended) A semiconductor device comprising:

first and second gates formed on active regions of a substrate, said first and second gates each consisting of a refractory metal layer on a polysilicon layer;

a field oxide formed on the substrate between said first and second gates;

side walls formed on side surfaces of said first and second gates, said side walls

being a silicon oxide film;

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